

applications of Ni₃Al-based alloys the authors recommend further research and development in a number of specific areas of the structure-property-processing relationships (Chapter 2).

Given the ambitious scope of the project and the "exponential proliferation" in the number of research papers on intermetallic compounds in the past decade, it was perhaps inevitable that this collective work would omit some key papers, particularly in fast-growing areas such as point defects and diffusion (Volume 1), and gamma TiAl and its alloys (Volume 2). Despite this shortcoming, this treatise's comprehensive discussion of crystal structure, the utility of its subject and author indexes and lists of acronyms and nomenclature, and the innovation of its index of compounds should significantly enhance further intermetallics research and development over the next few decades and should guarantee that this work will remain one of the key references on intermetallic compounds for a long time to come.

Reviewer: Man H. Yoo is a senior research staff member in the Metals and Ceramics Division, Oak Ridge National Laboratory. His research work includes physical properties and mechanical behavior of structural materials including intermetallic compounds.

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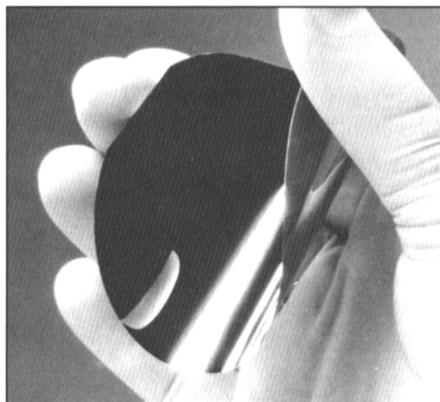
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